

## 2 Amp. Glass Passivated Avalanche Ultrafast Diode

<p>Dimensions in mm.</p> <p style="text-align: right;">DO-15 (Plastic)</p>	<p>Voltage 50 to 400 V.</p> <p>Current 2 A at 55 °C.</p>
<p><b>Mounting instructions</b></p> <ol style="list-style-type: none"> <li>1. Min. distance from body to soldering point, 4 mm.</li> <li>2. Max. solder temperature, 350 °C.</li> <li>3. Max. soldering time, 3.5 sec.</li> <li>4. Do not bend lead at a point closer than 2 mm. to the body.</li> </ol>	<ul style="list-style-type: none"> <li>• Glass Passivated Junction</li> <li>• High current capability</li> <li>• The plastic material carries U/L recognition 94 V-0</li> <li>• Terminals: Axial Leads</li> <li>• Polarity: Color band denotes cathode</li> </ul>

### Maximum Ratings, according to IEC publication No. 134

		EGP20A	EGP20B	EGP20D	EGP20F	EGP20G
$V_{RRM}$	Peak Recurrent reverse voltage (V)	50	100	200	300	400
$V_{RMS}$	Maximum RMS voltage	35	70	140	210	280
$V_{DC}$	Maximum DC blocking voltage	50	100	200	300	400
$I_{F(AV)}$	Forward current at Tamb = 55 °C	2 A				
$I_{FRM}$	Recurrent peak forward current	20 A				
$I_{FSM}$	8.3 ms. peak forward surge current (Jedec Method)	75 A				
$t_{rr}$	Max. reverse recovery time from $I_F = 0.5 A$ ; $I_R = 1 A$ ; $I_{RR} = 0.25 A$	50 ns				
$C_j$	Typical Junction Capacitance at 1 MHz and reverse voltage of $4V_{DC}$	45 pF			30 pF	
$T_j$	Max. operating temperature	+ 150 °C				
$T_{stg}$	Storage temperature range	- 65° to + 150 °C				
$E_{RSM}$	Maximum non repetitive peak reverse avalanche energy. $I_R = 1 A$ ; $T_j = 25 °C$	20 mJ				

### Electrical Characteristics at Tamb = 25 °C

$V_f$	Max. forward voltage drop at $I_F = 2 A$	0.95 V	1.25 V
$I_R$	Max. reverse current at $V_{RRM}$ at 25 °C at 150 °C	5 $\mu A$ 50 $\mu A$	
$R_{thj-a}$	Max. thermal resistance (l = 10 mm.)	30 °C/W	

## Rating And Characteristic Curves

